

ABSTRACT OF THE DISCLOSURE

A semiconductor device of the present invention includes a semiconductor substrate including an active region and an isolating region provided so as to enclose the active region; a capacitance insulating film that is provided on the active region and has a boundary portion in contact with the isolating region; an upper electrode provided on the capacitance insulating film so as to be spaced away from the isolating region; an electrode pad provided on the isolating region; a lead conductive film provided over a part of the capacitance insulating film and a part of the isolating region for connecting the upper electrode and the electrode pad; and an interlayer insulating film provided over the substrate. Connection holes penetrating the interlayer insulating film to reach the electrode pad are formed, and the ratio of the total sum of the exposed areas of the electrode pad in the contact holes with respect to the total sum of the widths of the lead conductive films in the boundary portion is a certain value or less.